

NJT4031N

Bipolar Power Transistors

NPN Silicon

Features

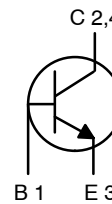
- Collector -Emitter Sustaining Voltage –
 $V_{CE(sus)} = 40 \text{ Vdc (Min) @ } I_C = 10 \text{ mAdc}$
- High DC Current Gain –
 $h_{FE} = 200 \text{ (Min) @ } I_C = 1.0 \text{ Adc}$
 $= 100 \text{ (Min) @ } I_C = 3.0 \text{ Adc}$
- Low Collector -Emitter Saturation Voltage –
 $V_{CE(sat)} = 0.150 \text{ Vdc (Max) @ } I_C = 1.0 \text{ Adc}$
 $= 0.300 \text{ Vdc (Max) @ } I_C = 3.0 \text{ Adc}$
- SOT-223 Surface Mount Packaging
- Epoxy Meets UL 94, V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B; > 8000 V
Machine Model, C; > 400 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



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NPN TRANSISTOR
3.0 AMPERES
40 VOLTS, 2.0 WATTS

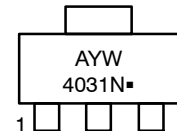


Schematic

MARKING DIAGRAM

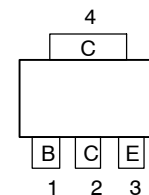


SOT-223
CASE 318E
STYLE 1



A = Assembly Location
Y = Year
W = Work Week
4031N = Specific Device Code
▪ = Pb-Free Package

PIN ASSIGNMENT



Top View Pinout

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NJT4031N

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CB}	40	Vdc
Emitter-Base Voltage	V _{EB}	6.0	Vdc
Base Current – Continuous	I _B	1.0	Adc
Collector Current – Continuous – Peak	I _C	3.0 5.0	Adc
Total Power Dissipation Total P _D @ T _A = 25°C mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material Total P _D @ T _A = 25°C mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material	P _D	2.0 0.80	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case – Junction-to-Ambient on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material – Junction-to-Ambient on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material	R _{θJA} R _{θJA}	64 155	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T _L	260	°C

ORDERING INFORMATION

Device	Package	Shipping†
NJT4031NT1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
NJT4031NT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NJT4031N

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0 \text{ Adc}$)	$V_{CEO(sus)}$	40			Vdc
Emitter-Base Voltage ($I_E = 50 \mu\text{Adc}$, $I_C = 0 \text{ Adc}$)	V_{EBO}	6.0			Vdc
Collector Cutoff Current ($V_{CB} = 40 \text{ Vdc}$)	I_{CBO}			100	nAdc
Emitter Cutoff Current ($V_{BE} = 6.0 \text{ Vdc}$)	I_{EBO}			100	nAdc

ON CHARACTERISTICS (Note 1)

Collector-Emitter Saturation Voltage ($I_C = 0.5 \text{ Adc}$, $I_B = 5.0 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 10 \text{ mAdc}$) ($I_C = 3.0 \text{ Adc}$, $I_B = 0.3 \text{ Adc}$)	$V_{CE(sat)}$			0.100 0.150 0.300	Vdc
Base-Emitter Saturation Voltage ($I_C = 1.0 \text{ Adc}$, $I_B = 0.1 \text{ Adc}$)	$V_{BE(sat)}$			1.0	Vdc
Base-Emitter On Voltage ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	$V_{BE(on)}$			1.0	Vdc
DC Current Gain ($I_C = 0.5 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 3.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	220 200 100		500	

DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_{ob}		25		pF
Input Capacitance ($V_{EB} = 5.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_{ib}		170		pF
Current-Gain - Bandwidth Product (Note 2) ($I_C = 500 \text{ mA}$, $V_{CE} = 10 \text{ V}$, $F_{test} = 1.0 \text{ MHz}$)	f_T		215		MHz

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.
2. $f_T = |h_{FE}| \cdot f_{test}$

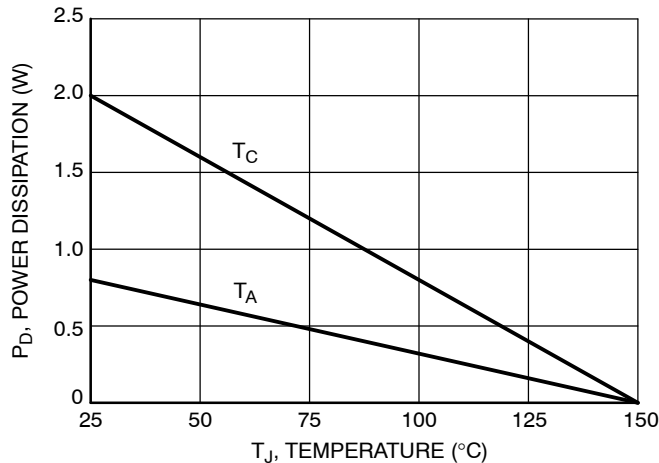


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

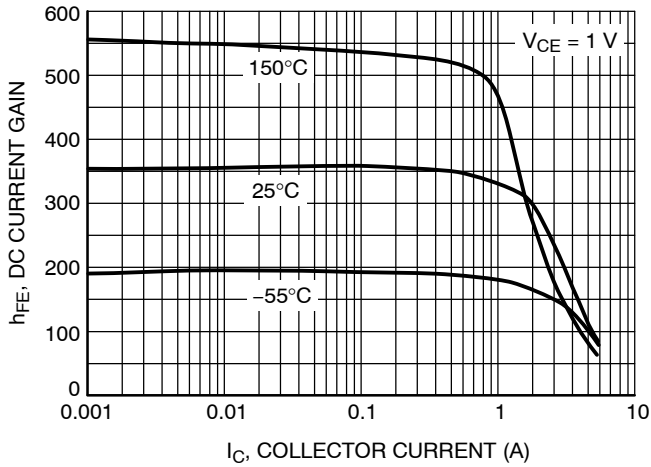


Figure 2. DC Current Gain

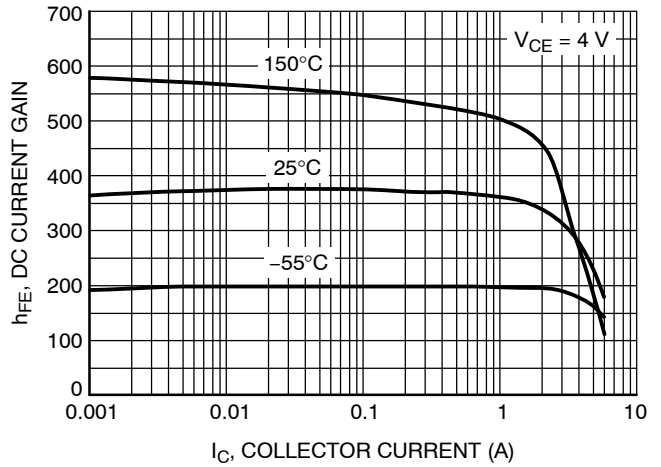


Figure 3. DC Current Gain

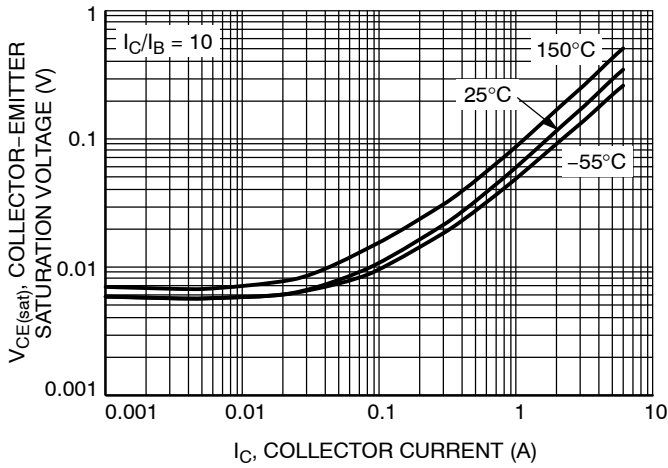


Figure 4. Collector-Emitter Saturation Voltage

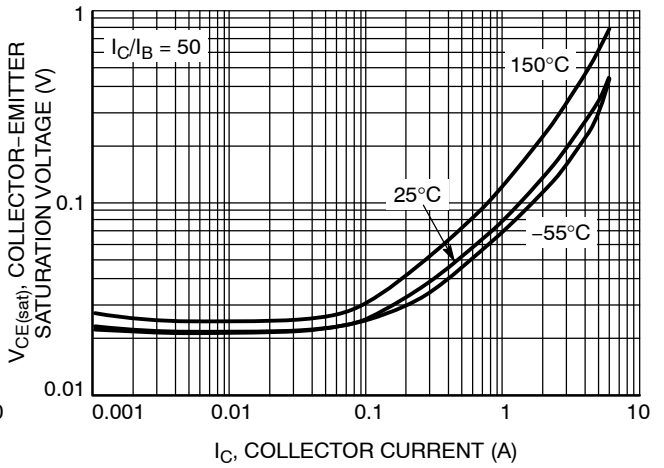


Figure 5. Collector-Emitter Saturation Voltage

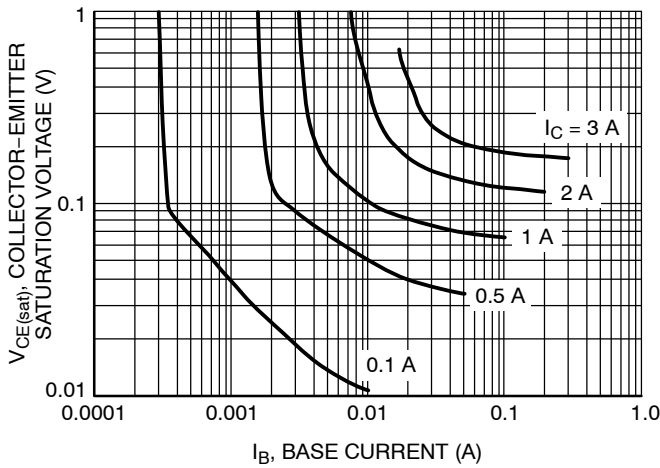


Figure 6. Collector Saturation Region

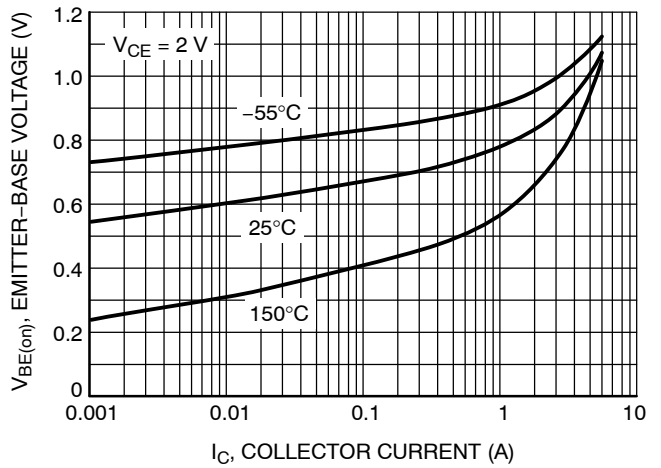


Figure 7. $V_{BE(on)}$ Voltage

TYPICAL CHARACTERISTICS

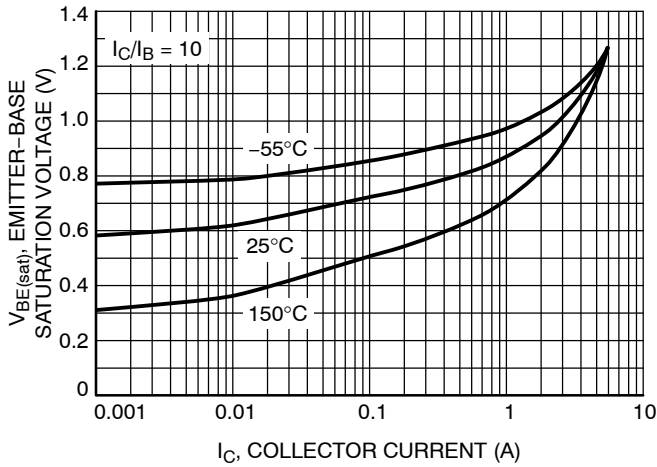


Figure 8. Base-Emitter Saturation Voltage

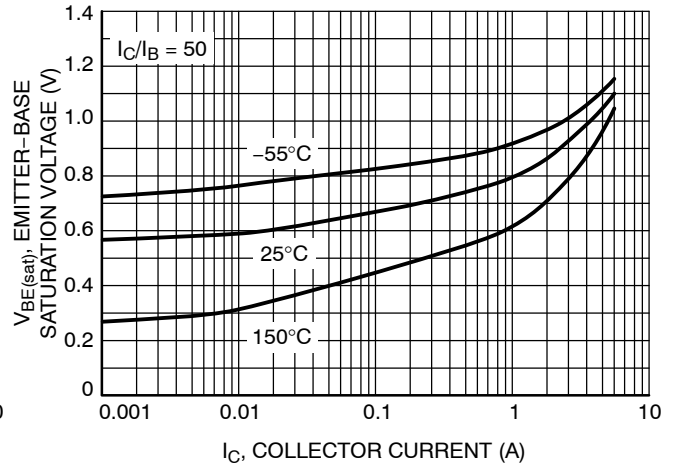


Figure 9. Base-Emitter Saturation Voltage

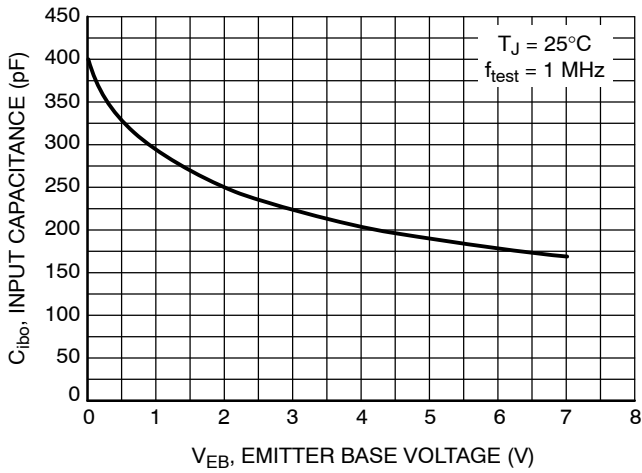


Figure 10. Input Capacitance

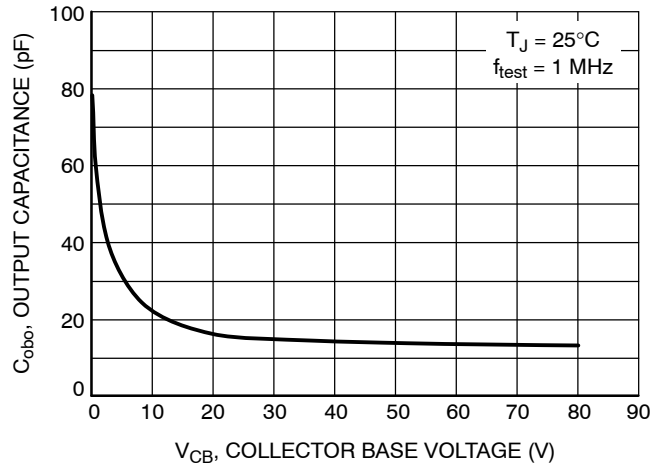


Figure 11. Output Capacitance

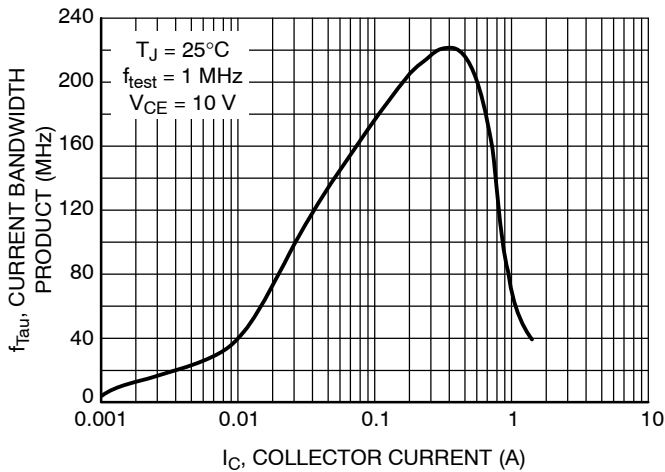


Figure 12. Current-Gain Bandwidth Product

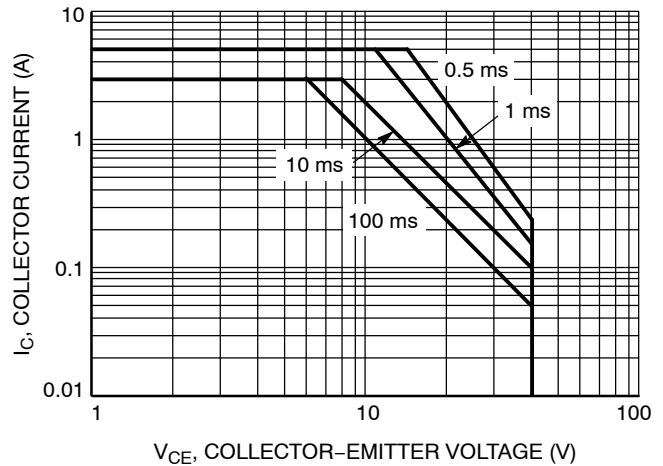
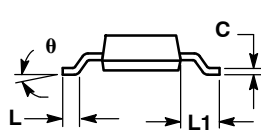
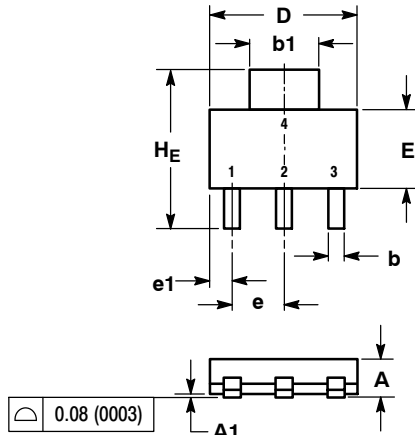


Figure 13. Safe Operating Area

NJT4031N

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE N

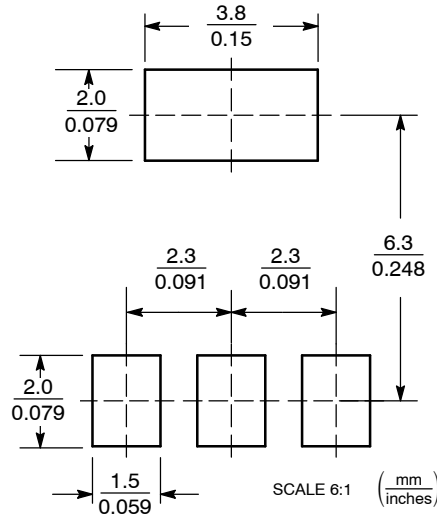


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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